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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/531,442	03/01/2006	Mun-Pyo Hong	PNK-0242	7000
23413 CANTOR COL	7590 06/27/200 BURN, LLP	EXAMINER		
20 Church Stree		POMPEY, RON EVERETT		
	22nd Floor Hartford, CT 06103			PAPER NUMBER
			2812	
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)
	10/531,442	HONG ET AL.
Office Action Summary	Examiner	Art Unit
	RON E. POMPEY	2812
The MAILING DATE of this communication ap Period for Reply	opears on the cover sheet with the o	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPLAY WHICHEVER IS LONGER, FROM THE MAILING IDENTIFY OF THE MAILING	DATE OF THIS COMMUNICATION .136(a). In no event, however, may a reply be tired will apply and will expire SIX (6) MONTHS from the, cause the application to become ABANDONE	N. mely filed the mailing date of this communication. ED (35 U.S.C. § 133).
Status		
Responsive to communication(s) filed on <u>08 and 08 a</u>	is action is non-final. ance except for formal matters, pro	
Disposition of Claims		
4) Claim(s) 1-14 is/are pending in the applicatio 4a) Of the above claim(s) 5-12 is/are withdrav 5) Claim(s) is/are allowed. 6) Claim(s) 1-4,13 and 14 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/ Application Papers 9) The specification is objected to by the Examir 10) The drawing(s) filed on is/are: a) according to the application and/	wn from consideration. /or election requirement. ner.	Examiner.
Applicant may not request that any objection to the Replacement drawing sheet(s) including the corre	ction is required if the drawing(s) is ob	ejected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreig a) All b) Some * c) None of: 1. Certified copies of the priority documer 2. Certified copies of the priority documer 3. Copies of the certified copies of the pri application from the International Bure: * See the attached detailed Office action for a list	nts have been received. nts have been received in Applicat ority documents have been receive au (PCT Rule 17.2(a)).	ion No ed in this National Stage
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:	ate

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DETAILED ACTION

<u>Examiner's Note:</u> the only changes to the mailing, 1/9/08, is correction to the PTOL-326 to have only box 2b checked.

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-4 and 13-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kim et al. (US 6091466), in view of Kim (US 6624871).

Kim('466) discloses the limitations of:

Claim 1. A thin film transistor array panel comprising:

an insulating substrate (101, fig. 5A)

a gate wire formed on the substrate and including a gate line (113/113a, fig. 5B) and a gate electrode (111, fig. 5B) connected to the gate line (fig. 4);

a gate insulating layer (117, fig. 5C) formed on the gate line; a semiconductor layer (133, fig. 5C) formed on the gate insulating layer;

a data wire formed on the semiconductor layer and including a data line (123, fig. 5D) intersecting the gate line (fig. 4), a source electrode (121, fig. 5D) connected to the data line, and a drain electrode (131, fig. 5D) located opposite the source electrode with respect to the gate electrode;

a pixel electrode (141, fig. 5F) connected to the drain electrode; and

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an etching assistant pattern (133a, fig. 5C) made of the same layer as the semiconductor pattern (133, fig. 5C) and located out of an area defined by intersections of the gate line and the data line (fig. 4), wherein the etching assistant pattern is extended from the semiconductor layer (col.5, ln. 15 – col. 6, ln. 37).

Claim 2. The thin film transistor array panel of claim 1, wherein the data wire (123/121/131, fig. 5D) comprises a lower film of Cr, Mo or Mo ally (col. 5, In. 53-60).

Claim 3. The thin film transistor array panel of claim 2, further comprising a passivation layer (137, fig. 5D) disposed between the data wire and the pixel electrode.

Claim 4. The thin film transistor array panel of claim 3, wherein the semiconductor layer has substantially the same planar shape as the data wire except for a channel portion located between the data line and the drain electrode.

- 13. The thin film transistor array panel of claim 1, wherein the etching assistant pattern is located outside of a pixel area (133, fig. 4).
- 14. The thin film transistor array panel of claim 1, wherein the etching assistant pattern is formed directly on the gate insulating layer (133, fig. 5C).
- Kim ('466), as indicated above, discloses all the features of the claims except:
 Claim 2. The thin film transistor array panel of claim 1, wherein the data wire
 comprises an upper film of AI or AI ally.
 - a. However, Kim('871) discloses:

The thin film transistor array panel of claim 1, wherein the data wire comprises a lower film of Cr, Mo or Mo ally and an upper film of AI or AI ally (35S/35D/35P/35L, fig. 4A; col. 4, Ins. 28-31 Kim).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify the data wire in Kim ('466), with the dual layer with a lower film of Cr, Mo or Mo ally and an upper film of AI or AI ally as taught by Kim('871), because the AI provides for excellent electrical conductivity of the data wire.

Response to Arguments

2. Applicant's arguments with respect to claims 1-4 and 13-14, received 10-30-07, have been considered but are moot in view of the new ground(s) of rejection.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to RON E. POMPEY whose telephone number is (571)272-1680. The examiner can normally be reached on 9AM - 5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Charles Garber can be reached on (571) 272-2194. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information

system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Walter L. Lindsay, Jr./
Primary Examiner, Art Unit 2812

Ron Pompey AU: 2812 1/4/08